

V _{CES}	650V
I _{C (100°C)}	50A
V _{CE(sat) (Typ.)}	1.6V
P _D	245W

Features

- 1) Low Collector Emitter Saturation Voltage
- 2) High Speed Switching
- 3) Low Switching Loss & Soft Switching
- 4) Built in Very Fast & Soft Recovery FRD
- 5) Pb free Lead Plating ; RoHS Compliant

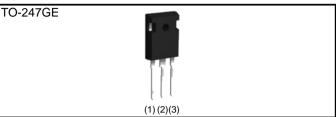
Application

PFC

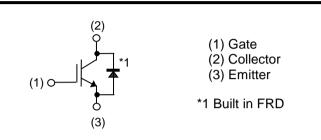
Solar converters

Mid to high switching frequency converters

Outline



Inner Circuit



Packaging Specifications

Packaging	Tube
Reel Size (mm)	-
Tape Width (mm)	-
Basic Ordering Unit (pcs)	600
Packing Code	C13
Marking	RGWS00TS65D
	Reel Size (mm) Tape Width (mm) Basic Ordering Unit (pcs) Packing Code

•Absolute Maximum Ratings (at T_C = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V _{CES}	650	V
Gate - Emitter Voltage		V _{GES}	±30	V
Collector Current	$T_{\rm C} = 25^{\circ}{\rm C}$	Ι _C	88	Α
Collector Current	$T_{\rm C} = 100^{\circ}{\rm C}$	Ι _C	54	Α
Pulsed Collector Current		I _{CP} *1	150	Α
Diada Farward Currant	$T_{\rm C} = 25^{\circ}{\rm C}$	١ _F	23	Α
Diode Forward Current	$T_{\rm C} = 100^{\circ}{\rm C}$	١ _F	13	Α
Diode Pulsed Forward Current		I _{FP} ^{*1}	60	Α
Dower Dissipation	$T_{\rm C} = 25^{\circ}{\rm C}$	P _D	245	W
Power Dissipation	$T_{\rm C} = 100^{\circ}{\rm C}$	P _D	121	W
Operating Junction Temperature		Tj	-40 to +175	°C
Storage Temperature		T _{stg}	-55 to +175	°C

*1 Pulse width limited by T_{jmax.}

Thermal Resistance

Deremeter	Symbol	Values			Unit
Parameter	Symbol	Min.	Тур.	Max.	
Thermal Resistance IGBT Junction - Case	$R_{\theta(j\text{-}c)}$	-	-	0.61	°C/W
Thermal Resistance Diode Junction - Case	$R_{\theta(j-c)}$	-	-	2.88	°C/W

•IGBT Electrical Characteristics (at $T_j = 25^{\circ}C$ unless otherwise specified)

Parameter	Symbol Conditions -		Values			Unit
Farameter			Min.	Тур.	Max.	Unit
Collector - Emitter Breakdown Voltage	BV _{CES}	I _C = 10μΑ, V _{GE} = 0V	650	-	-	V
Collector Cut - off Current	I _{CES}	$V_{CE} = 650V, V_{GE} = 0V$	-	-	10	μA
Gate - Emitter Leakage Current	I _{GES}	$V_{GE} = \pm 30V, V_{CE} = 0V$	-	-	±200	nA
Gate - Emitter Threshold Voltage	$V_{\text{GE(th)}}$	V _{CE} = 5V, I _C = 26.0mA	5.0	6.0	7.0	V
Collector - Emitter Saturation Voltage	V _{CE(sat)}	$I_{C} = 50A, V_{GE} = 15V,$ $T_{j} = 25^{\circ}C$ $T_{j} = 175^{\circ}C$	-	1.6 2.0	2.0 -	V



Parameter	Symbol	O and ditions a	Values			11
		Conditions	Min.	Тур.	Max.	Unit
Input Capacitance	C _{ies}	V _{CE} = 30V,	-	3320	-	
Output Capacitance	C _{oes}	V _{GE} = 0V,	-	83	-	pF
Reverse transfer Capacitance	C _{res}	f = 1MHz	-	60	-	
Total Gate Charge	Qg	V _{CE} = 400V,	-	108	-	
Gate - Emitter Charge	Q _{ge}	I _C = 50A,	-	22	-	nC
Gate - Collector Charge	Q_{gc}	V _{GE} = 15V	-	42	-	
Turn - on Delay Time	t _{d(on)}	$I_{C} = 50A, V_{CC} = 400V,$ $V_{GE} = 15V, R_{G} = 10\Omega,$ $T_{i} = 25^{\circ}C$	-	46	-	
Rise Time	t _r		-	20	-	ns
Turn - off Delay Time	t _{d(off)}		-	145	-	
Fall Time	t _f	Inductive Load	-	38	-	
Turn - on Switching Loss	E_{on}	*E _{on} include diode reverse recovery	-	0.98	-	mJ
Turn - off Switching Loss	E_{off}		-	0.91	-	mJ
Turn - on Delay Time	t _{d(on)}		-	43	-	
Rise Time	t _r	$I_{C} = 50A, V_{CC} = 400V,$ $V_{GE} = 15V, R_{G} = 10\Omega,$	-	24	-	n 0
Turn - off Delay Time	t _{d(off)}	$T_i = 175^{\circ}C$	-	165	-	ns
Fall Time	t _f	Inductive Load	-	78	-	
Turn - on Switching Loss	E_{on}	*E _{on} include diode reverse recovery	-	1.02	-	~ 1
Turn - off Switching Loss	E_{off}		-	1.19	-	mJ
Reverse Bias Safe Operating Area	RBSOA	$I_{C} = 150A, V_{CC} = 520V$ $V_{P} = 650V, V_{GE} = 15V$ $R_{G} = 100\Omega, T_{j} = 175^{\circ}C$	FU	LL SQUA	RE	-

●IGBT Electrical Characteristics (at T_i = 25°C unless otherwise specified)



•FRD Electrical Characteristics (at $T_j = 25^{\circ}C$ unless otherwise specified)

Parameter	O. make at	Conditions	Values			
	Symbol		Min.	Тур.	Max.	Unit
		I _F = 10A,				
Diode Forward Voltage	V _F	T _j = 25°C	-	1.45	1.9	V
		T _j = 175°C	-	1.4	-	
Diode Reverse Recovery Time	t _{rr}	$I_F = 10A,$ $V_{CC} = 400V,$ $di_F/dt = 200A/\mu s,$ $T_j = 25^{\circ}C$	-	88	-	ns
Diode Peak Reverse Recovery Current	I _{rr}		-	5.9	-	A
Diode Reverse Recovery Charge	Q _{rr}		-	0.28	-	μC
Diode Reverse Recovery Energy	Err		-	17.6	-	μJ
Diode Reverse Recovery Time	t _{rr}	$I_F = 10A,$ $V_{CC} = 400V,$ $di_F/dt = 200A/\mu s,$ $T_j = 175^{\circ}C$	-	105	-	ns
Diode Peak Reverse Recovery Current	I _{rr}		-	6.9	-	А
Diode Reverse Recovery Charge	Q _{rr}		-	0.42	-	μC
Diode Reverse Recovery Energy	E _{rr}		-	28.8	-	μJ



•Electrical Characteristic Curves

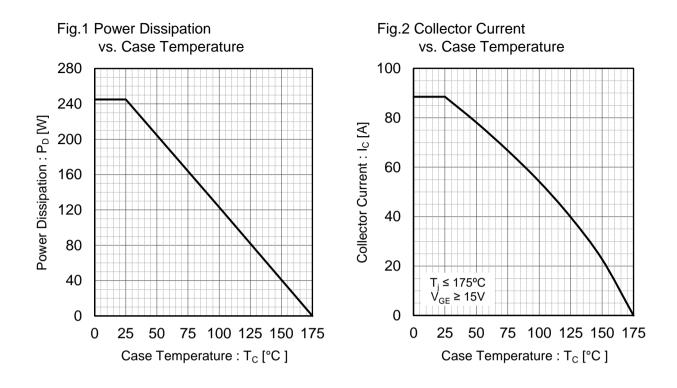
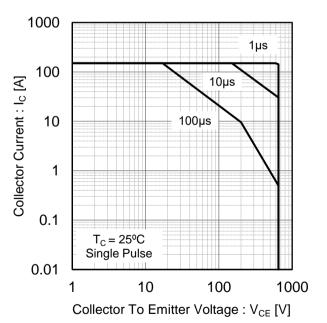
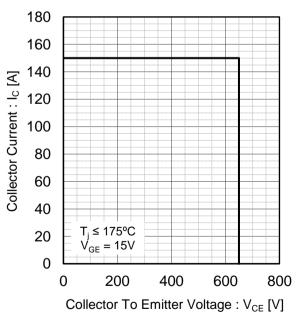


Fig.3 Forward Bias Safe Operating Area

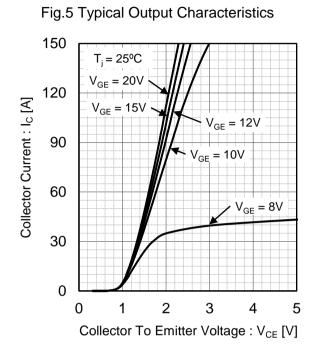








Electrical Characteristic Curves



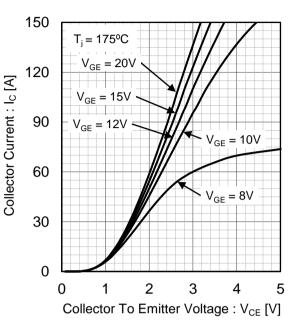
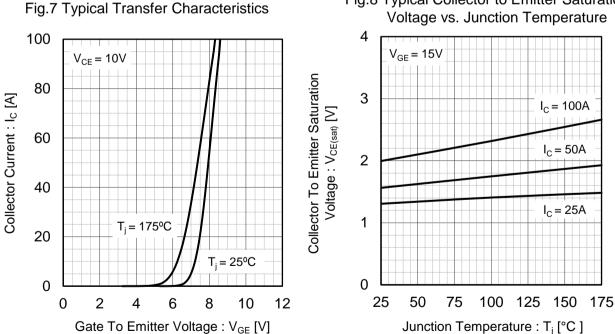
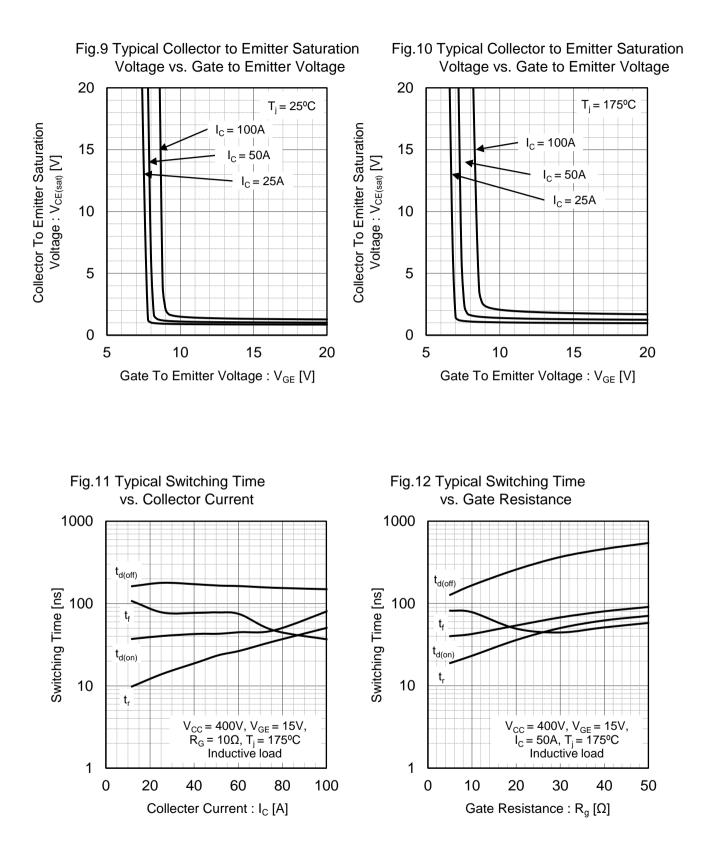


Fig.6 Typical Output Characteristics

Fig.8 Typical Collector to Emitter Saturation Voltage vs. Junction Temperature

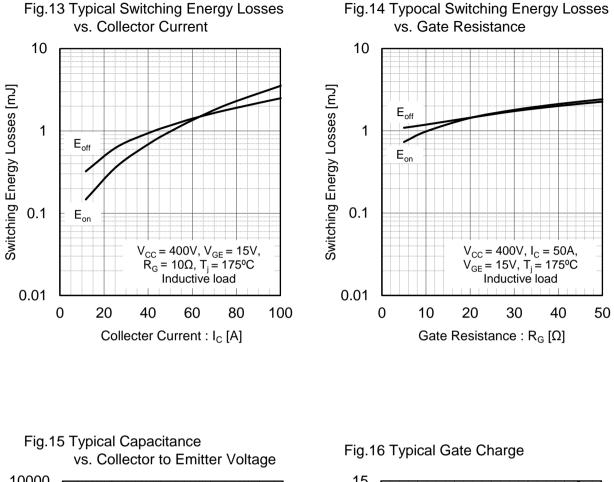


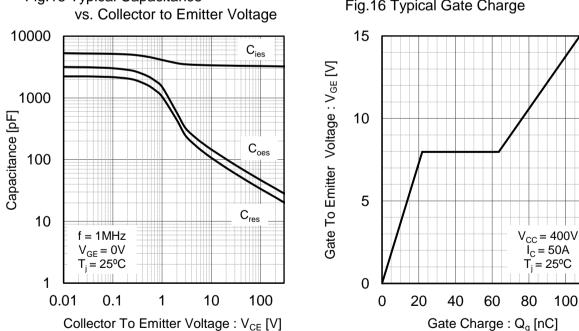
•Electrical Characteristic Curves





Electrical Characteristic Curves



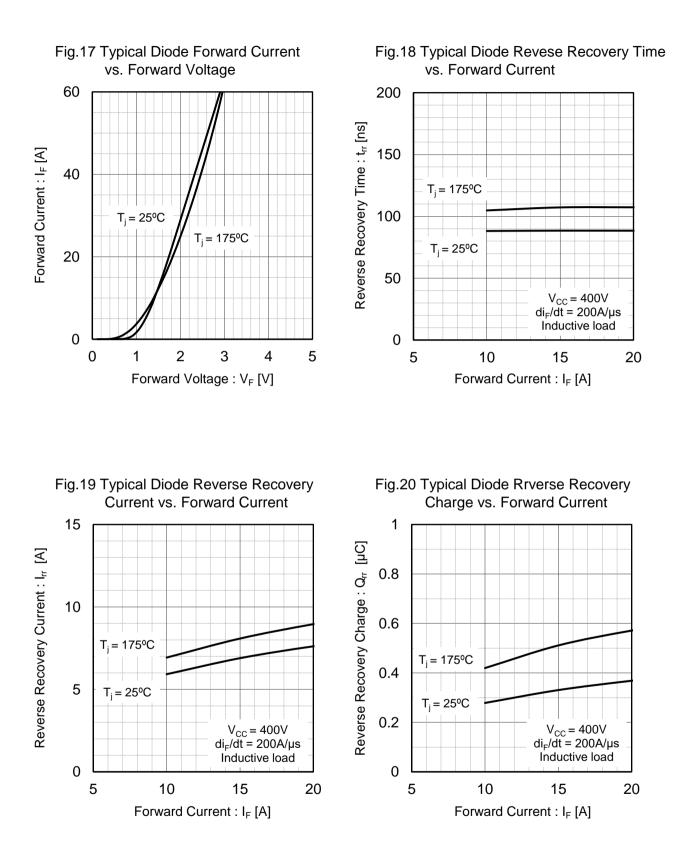




100

120

Electrical Characteristic Curves





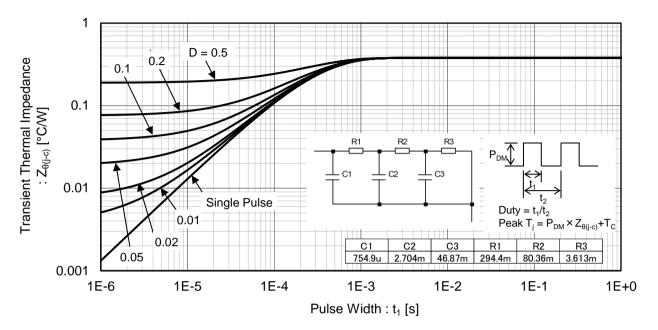
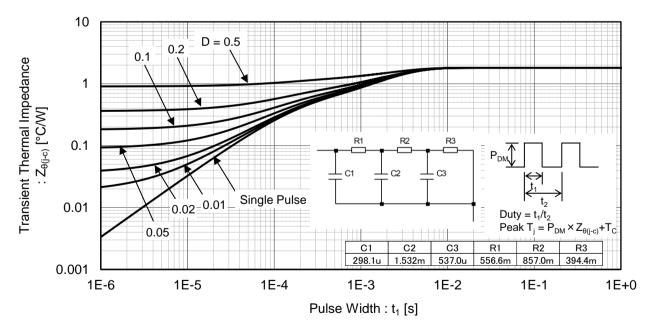


Fig.21 Typical IGBT Transient Thermal Impedance





●Inductive Load Switching Circuit and Waveform

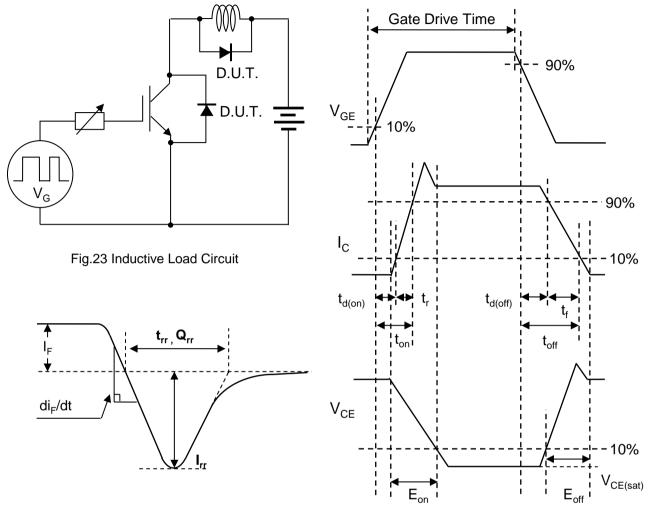


Fig.25 Diode Reverse Recovery Waveform

Fig.24 Inductive Load Waveform



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